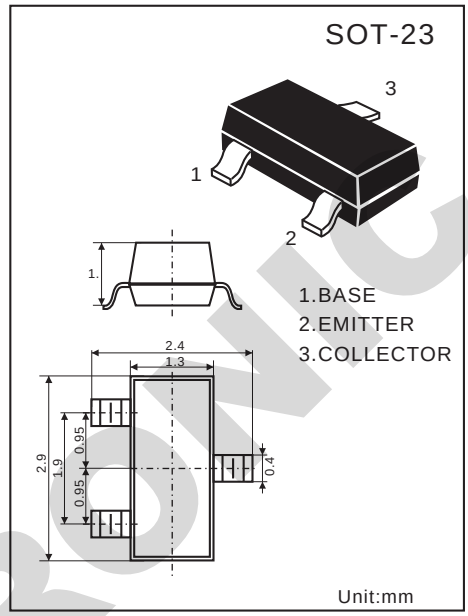
TRANSISTOR (NPN)



Features

- Power dissipation

  P_{CM} : 0.225 W (Tamb=25 C)

- Pluse Drain

  I_{CM} : -0.6 mA

- Reverse Voltage

  $V_{(BR)CBO}$: -40V

- Operating and storage junction temperature range

  T_j, T_{stg} : -55℃ to +150℃

Electrical Characteristics

(Ta=25℃)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-40			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1 mA, I_B=0	-40			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5			V
Collector Cut-off Current	I_{CBO}	V_{CB}=-35V, I_E=0			-0.1	μA
Collector Cut-off Current	I_{CEO}	V_{CB}=-35V, I_B=0			-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-4V, I_C=0			-0.1	μA
DC Current Gain (Note)	$H_{FE(1)}$	V_{CE}=-2V, I_C=-150mA	100		300	
	$H_{FE(2)}$	V_{CE}=-2V, I_C=-500mA	20			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-150mA, I_B=-15mA			-0.4	V
Base-emitter saturatio voltage	$V_{BE(sat)}$	I_C=-150mA, I_B=-15mA			-0.95	V
Transition Frequency	f_T	V_{CE}=-10V, I_C=-20mA ,f=100MHz	200			Mhz

Device Marking

MMBT4401LT1 = 2X

Typical Characteristics

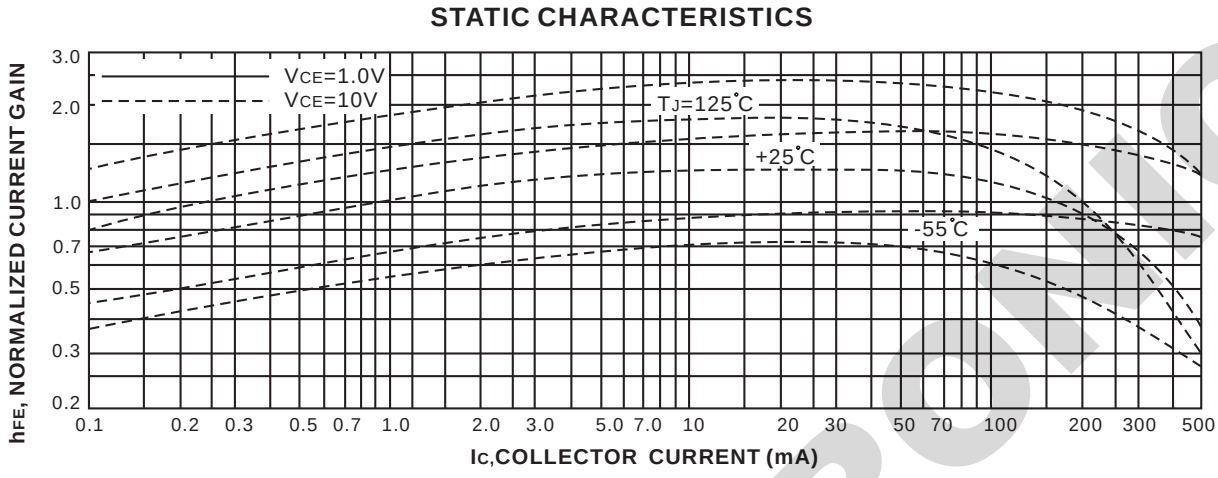


Figure 14.DC Current Gain

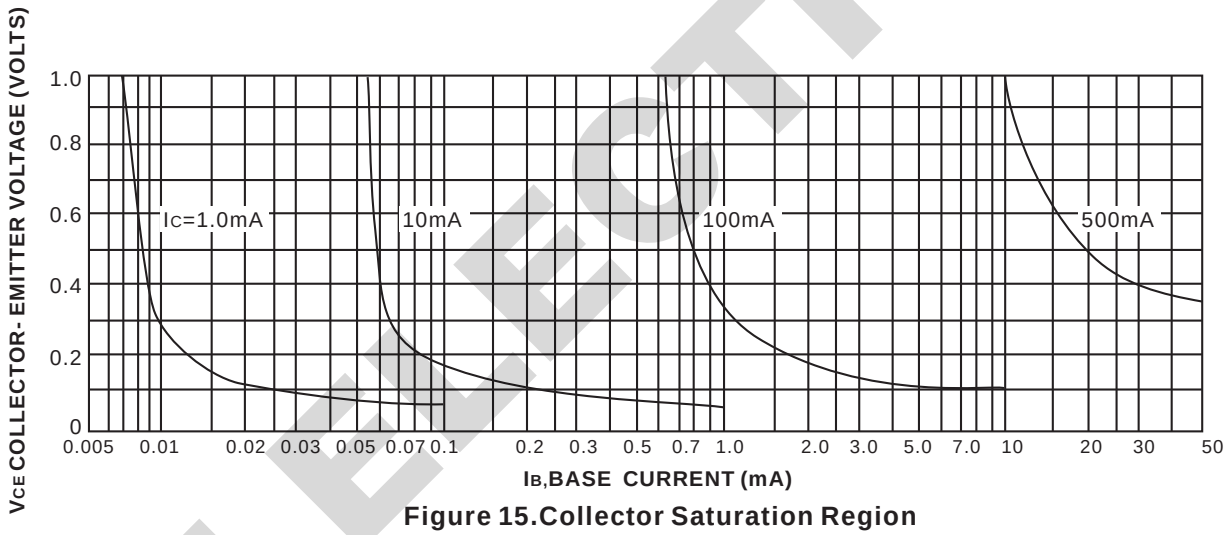


Figure 15.Collector Saturation Region

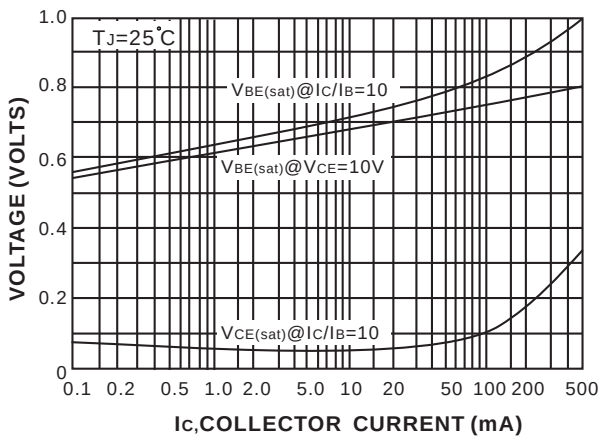


Figure 16. “On” Voltages